## **AMENDMENTS TO THE CLAIMS**

## 1-8. (Canceled)

- 9. (Currently amended) An FePt magnetic thin film having an atomic composition represented by the following Formula: Fe<sub>x</sub>Pt<sub>100-x</sub>, wherein 19 ≤ x ≤ 45, and having an L1<sub>0</sub> structure.
  (19 ≤ x ≤ 52).
- 10. (Currently amended) The FePt magnetic thin film according to Claim 9, having a thickness of less than 100 nm-and an L1<sub>0</sub> structure.
- 11. (Previously presented) The FePt magnetic thin film according to Claim 9, being formed on a single crystalline substrate or on an oxide undercoat layer formed on the surface thereof.
- 12. (Currently amended) The FePt magnetic thin film according to Claim 11, being formed via a thin layer of one or more <u>selected from the group consisting</u> of transition and noble metals formed as an undercoat layer.
- 13. (Previously presented) The FePt magnetic thin film according to Claim 12, wherein the thin layer is a single layer or multiple layers.
- 14. (Currently amended) The FePt magnetic thin film according to Claim 13, wherein the thin layer has a layer of one or more <u>selected from the group consisting</u> of Fe, Ag, Ni, Co and Cr, and a layer of one or more selected from the group consisting of Au, Pt, and Cu.

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- 15. (Withdrawn) A method of producing the FePt magnetic thin film according to claim 9, characterized by forming the FePt magnetic thin film by sputtering on a single crystalline substrate, a substrate having an oxide undercoat layer formed thereon, or a substrate having a thin layer of one or more of transition and noble metals as undercoat layer at a temperature in the range of 240°C to 500°C.
- 16. (Withdrawn) The method of producing the FePt magnetic thin film according to Claim 15, wherein the FePt magnetic thin film is formed by sputtering at a temperature of 300°C or lower.